

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

CM1293A-02SR

Product specification

Features

- 150Watts peak pulse power ($t_p = 8/20\mu s$)
- Tiny SOT-143 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance ($C_j = 1.5pF$ typ I/O to I/O.)
- Protection one data/power line to:
- IEC 61000-4-2 $\pm 15kV$ contact $\pm 20kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20 μs)

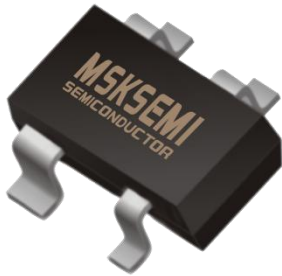

Mechanical Data

- SOT-143 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

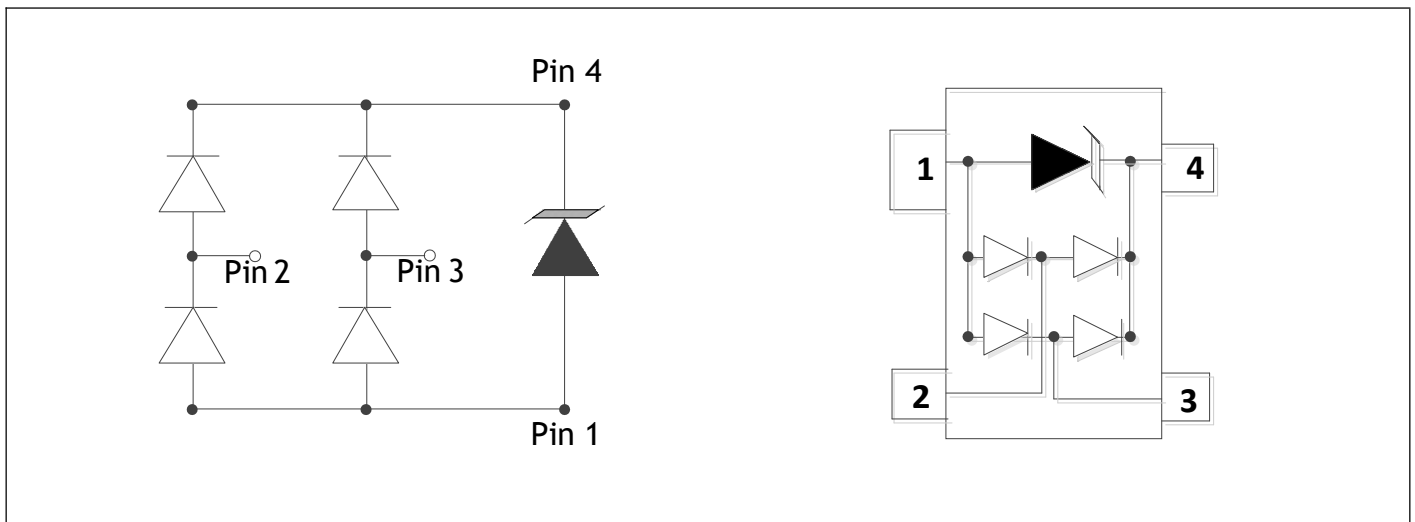
Applications

- USB2.0,
- Ethernet
- Notebooks, Desktops, and Servers
- Video Line Protection

Reference News

| SOT-143 | Marking |
|---|---|
|  |  |

Schematic & PIN Configuration



Absolute Maximum Rating

| Rating | Symbol | Value | Units |
|--|-----------|----------------|-------|
| Peak Pulse Power ($t_p = 8/20\mu s$) | P_{PP} | 150 | Watts |
| Peak Pulse Current ($t_p = 8/20\mu s$) (note1) | I_{pp} | 5 | A |
| ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact) | V_{ESD} | 20 15 | kV |
| Lead Soldering Temperature | T_L | 260(10seconds) | °C |
| Junction Temperature | T_J | -55 to + 125 | °C |
| Storage Temperature | T_{stg} | -55 to + 125 | °C |

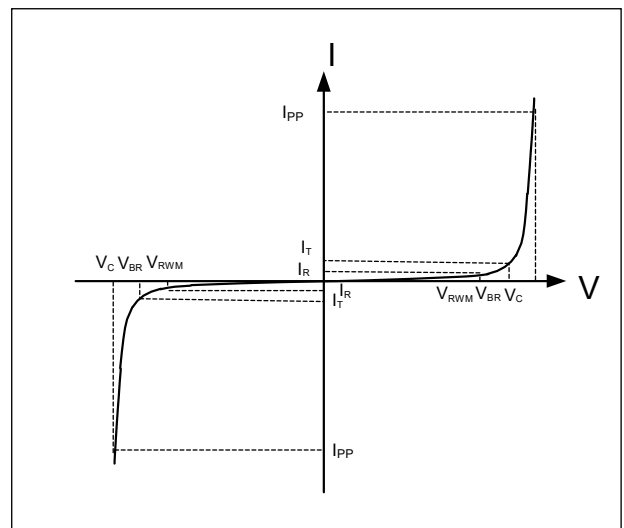
Electrical Characteristics

| Parameter | Symbol | Conditions | Min | Typical | Max | Units |
|---------------------------|-----------|-----------------------------------|-----|---------|-----|-------|
| Reverse Stand-Off Voltage | V_{RWM} | | | | 5.5 | V |
| Reverse Breakdown Voltage | V_{BR} | $I_r = 1mA$ | 6.0 | | | V |
| Reverse Leakage Current | I_R | $V_{RWM} = 5V, T = 25^\circ C$ | | | 500 | nA |
| Clamping Voltage | V_C | $I_{PP} = 5A, t_p = 8/20\mu s$ | | 14 | | V |
| Junction Capacitance | C_j | $V_R = 0V, f = 1MHz$ IO to IO | | 1.5 | | pF |
| | | $V_R = 0V, f = 1MHz$ IO to GND | | 1.0 | 2.0 | |

Electrical Parameters (TA = 25°C unless otherwise noted)

| Symbol | Parameter |
|-----------|---|
| I_{PP} | Maximum Reverse Peak Pulse Current |
| V_C | Clamping Voltage @ I_{PP} |
| V_{RWM} | Working Peak Reverse Voltage |
| I_R | Maximum Reverse Leakage Current @ V_{RWM} |
| V_{BR} | Breakdown Voltage @ I_r |
| I_r | Test Current |
| | |
| | |

Note: 8/20μs pulse waveform.



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

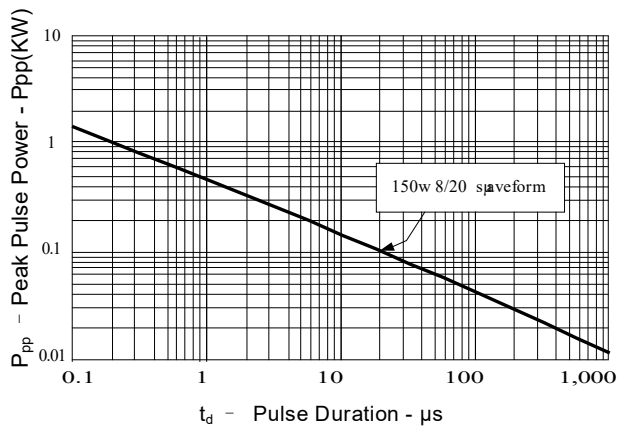


Figure 2: Power Derating Curve

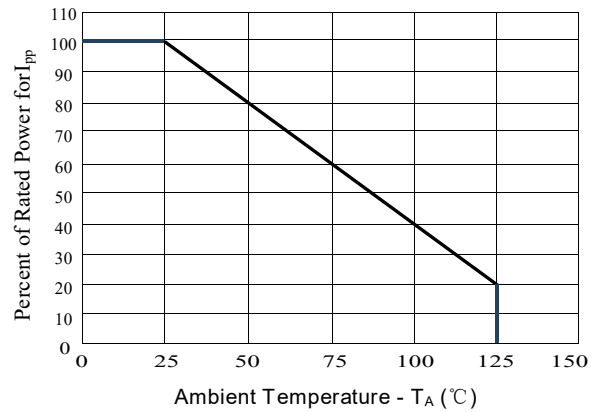


Figure3: Pulse Waveform

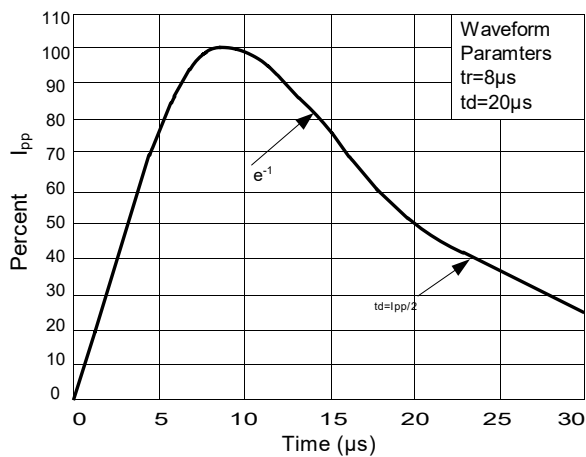
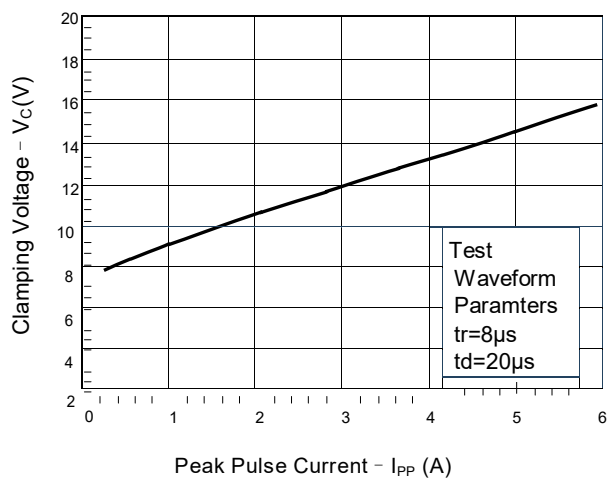
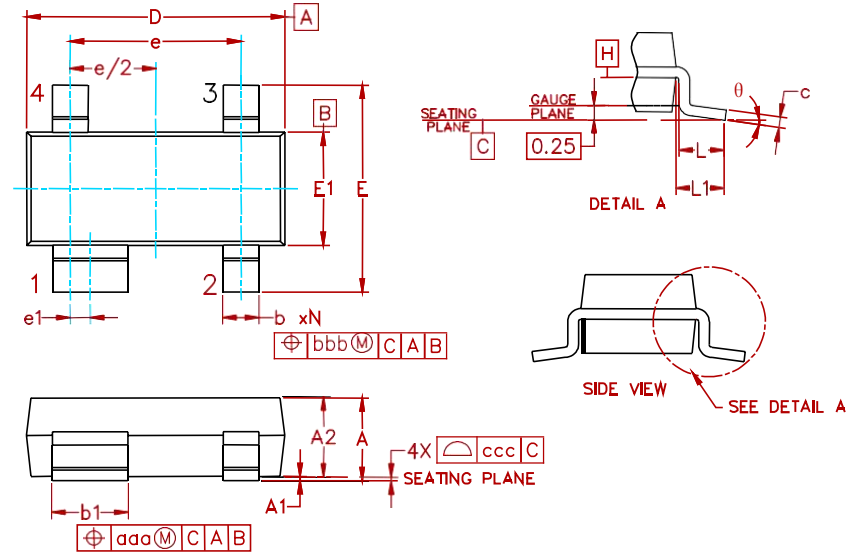


Figure 4: Clamping Voltage vs. Ipp

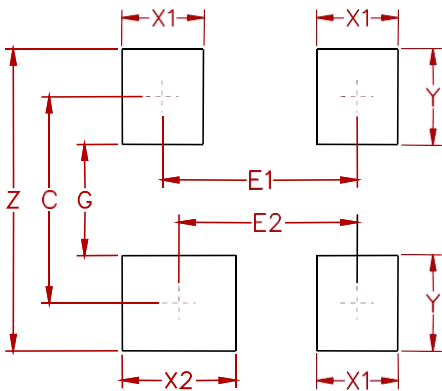


PACKAGE MECHANICAL DATA

| Symbol | Inches | | | Millimeters | | |
|--------|---------|-------|-------|-------------|------|------|
| | Min. | Nom. | Max. | Min. | Nom. | Max. |
| A | 0.031 | - | 0.048 | 0.80 | - | 1.22 |
| A1 | 0.000 | - | 0.008 | 0.013 | - | 0.15 |
| A2 | 0.020 | 0.035 | 0.042 | 0.75 | 0.90 | 1.07 |
| b | 0.011 | - | 0.020 | 0.30 | - | 0.51 |
| b1 | 0.029 | - | 0.037 | 0.76 | - | 0.94 |
| c | 0.003 | - | 0.008 | 0.08 | - | 0.20 |
| D | 0.110 | 0.114 | 0.120 | 2.80 | 2.90 | 3.04 |
| E | 0.082 | 0.093 | 0.104 | 2.10 | 2.37 | 2.64 |
| E1 | 0.047 | 0.051 | 0.055 | 1.20 | 1.30 | 1.40 |
| e | 0.075 | | | 1.92 BSC | | |
| e1 | 0.008 | | | 0.20 BSC | | |
| L | 0.015 | 0.020 | 0.024 | 0.40 | 0.50 | 0.60 |
| L1 | (0.021) | | | (0.54) | | |
| N | 4 | | | 4 | | |
| θ | 0° | - | 8° | 0° | - | 8° |
| aaa | 0.006 | | | 0.15 | | |
| bbb | 0.008 | | | 0.20 | | |
| ccc | 0.004 | | | 0.10 | | |



Suggested Pad Layout



Order information

| Orderable Device | Package | Packing Option |
|------------------|---------|----------------|
| CM1293A-02SR | SOT-143 | 3000PCS |

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